# NCE N-Channel Super Trench Power MOSFET

## Description

The NCEP60ND60G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and $Q_g$. This device is ideal for high-frequency switching and synchronous rectification.

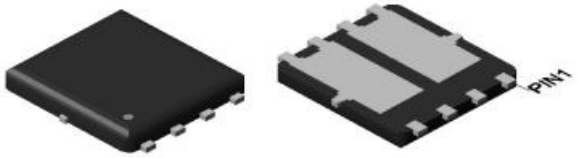
## Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

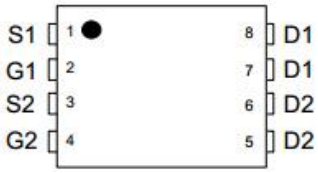
## General Features

- $V_{DS}$ =60V,$I_D$ =55A
  $R_{DS(ON)}$=7.8mΩ (typical) @ $V_{GS}$=10V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

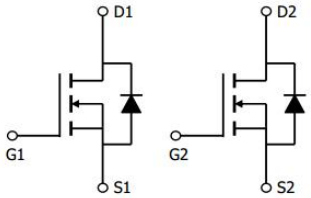
***100% UIS TESTED!***
***100% ΔVds TESTED!***




**DFN 5X6**




**Pin Assignment**




**Schematic Diagram**

## Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| P60ND60G | NCEP60ND60G | DFN5X6-8L | - | - | - |

## Absolute Maximum Ratings ($T_C$=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 60 | V |
| Gate-Source Voltage | $V_{GS}$ | ±20 | V |
| Drain Current-Continuous | $I_D$ | 55 | A |
| Drain Current-Continuous($T_C$=100℃) | $I_D$ (100℃) | 38.9 | A |
| Pulsed Drain Current | $I_{DM}$ | 220 | A |
| Maximum Power Dissipation | $P_D$ | 70 | W |
| Derating factor | | 0.56 | W/℃ |
| Single pulse avalanche energy (Note1) | $E_{AS}$ | 320 | mJ |
| Operating Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 To 150 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Resistance,Junction-to-Case | $R_{\theta JC}$ | 1.78 | ℃/W |

## Electrical Characteristics ($T_C$=25℃unless otherwise noted)

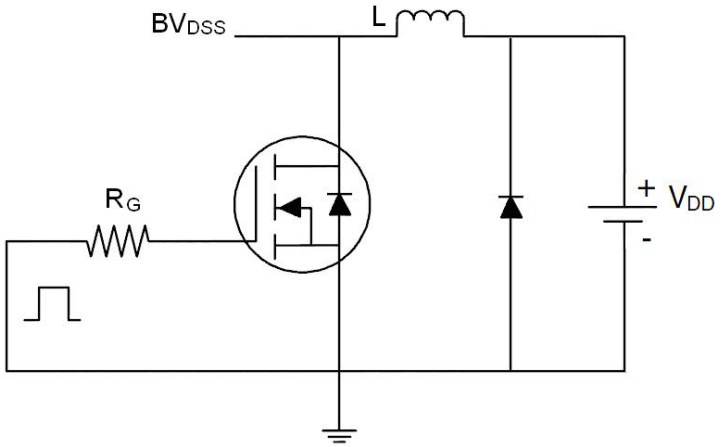
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 60 | | - | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=60V,$V_{GS}$=0V | - | - | 1 | μA |
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±20V,$V_{DS}$=0V | - | - | ±100 | nA |
| **On Characteristics** | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 2 | 3 | 4 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=20A | - | 7.8 | 8.5 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=5V,$I_D$=20A | 35 | - | - | S |
| **Dynamic Characteristics** | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=30V,$V_{GS}$=0V, F=1.0MHz | - | 1700 | - | PF |
| Output Capacitance | $C_{oss}$ | | - | 345 | - | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 40 | - | PF |
| **Switching Characteristics** (Note 2) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=30V,$I_D$=20A $V_{GS}$=10V,$R_G$=4.7Ω | - | 8 | - | nS |
| Turn-on Rise Time | $t_r$ | | - | 2 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 29 | - | nS |
| Turn-Off Fall Time | $t_f$ | | - | 4 | - | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=30V,$I_D$=20A, $V_{GS}$=10V | - | 28.5 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 9.4 | | nC |
| Gate-Drain Charge | $Q_{gd}$ | | - | 6 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage | $V_{SD}$ | $V_{GS}$=0V,$I_S$=20A | - | | 1.2 | V |
| Diode Forward Current | $I_S$ | | - | - | 55 | A |
| Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25°C, $I_F$ = $I_S$ di/dt = 100A/μs | - | 38 | | nS |
| Reverse Recovery Charge | Qrr | | - | 48 | | nC |

## Notes:

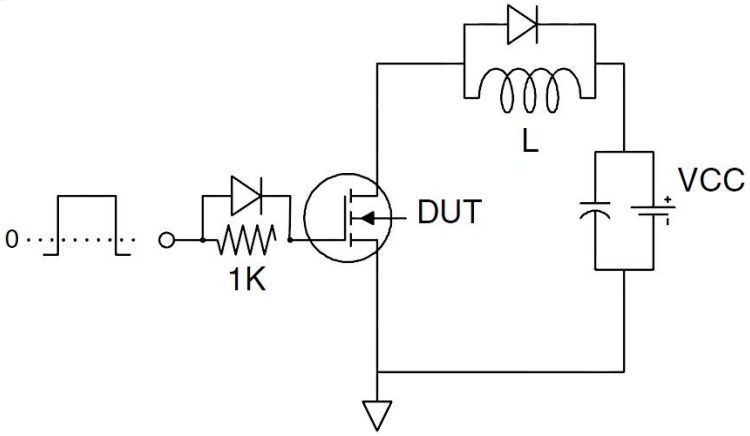
1. EAS condition : Tj=25℃,$V_{DD}$=30V,$V_G$=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating.

## Test Circuit

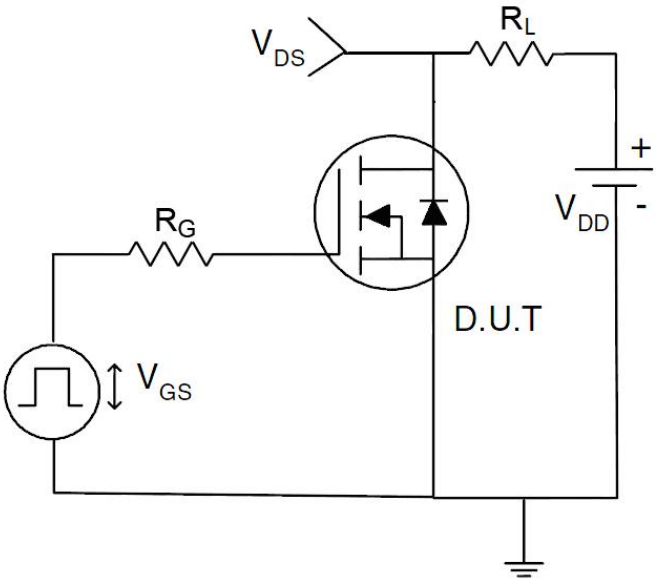
### 1) $E_{AS}$ test Circuit




### 2) Gate charge test Circuit




### 3) Switch Time Test Circuit



## Typical Electrical and Thermal Characteristics

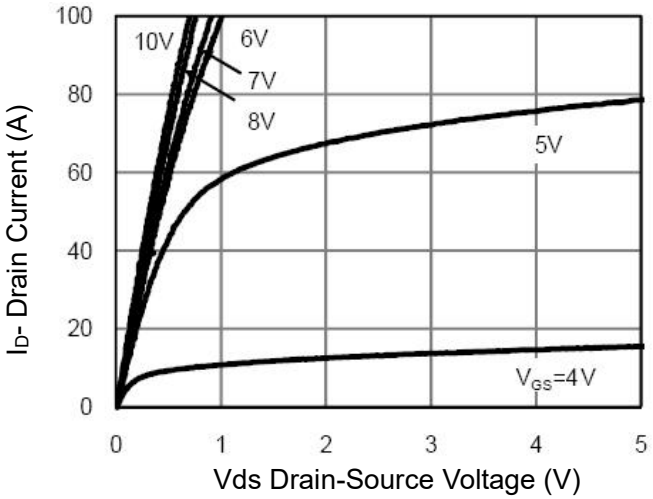



**Figure 1 Output Characteristics**

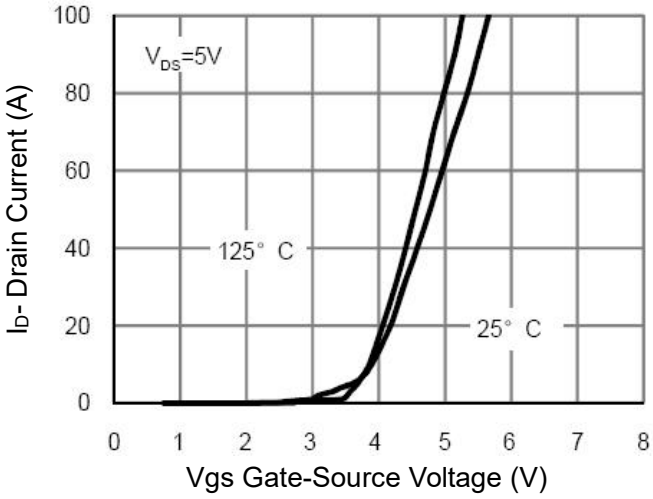



**Figure 2 Transfer Characteristics**

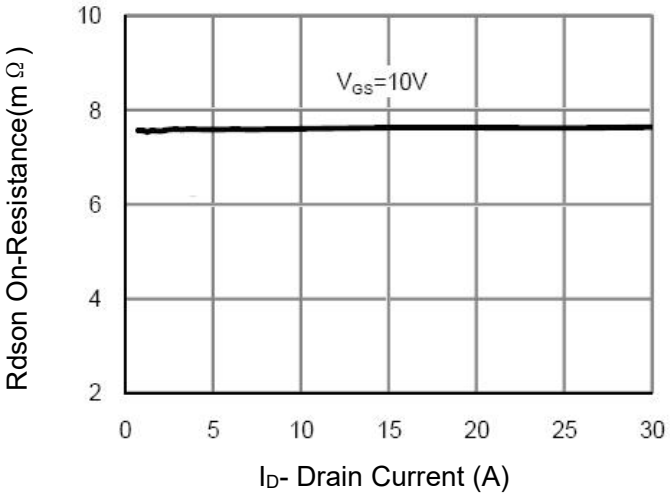



**Figure 3 Rdson- Drain Current**

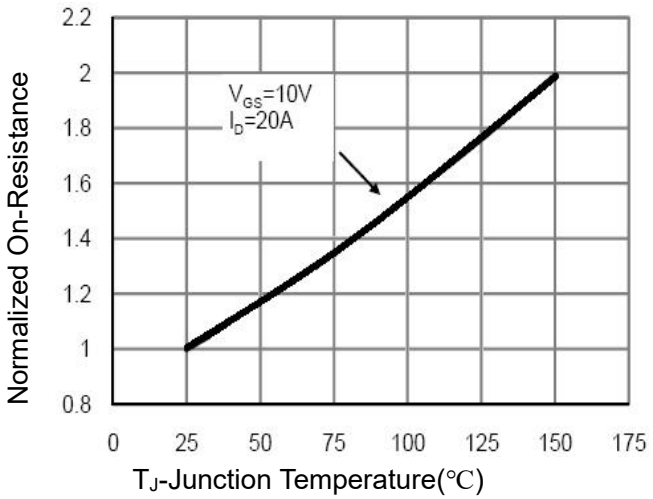



**Figure 4 Rdson-JunctionTemperature**

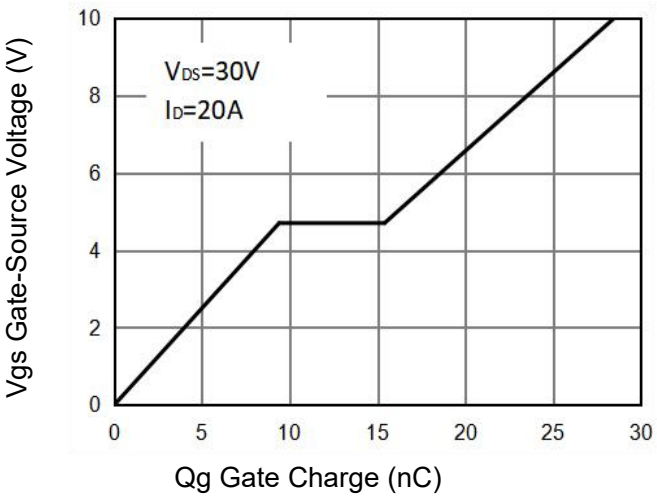



**Figure 5 Gate Charge**

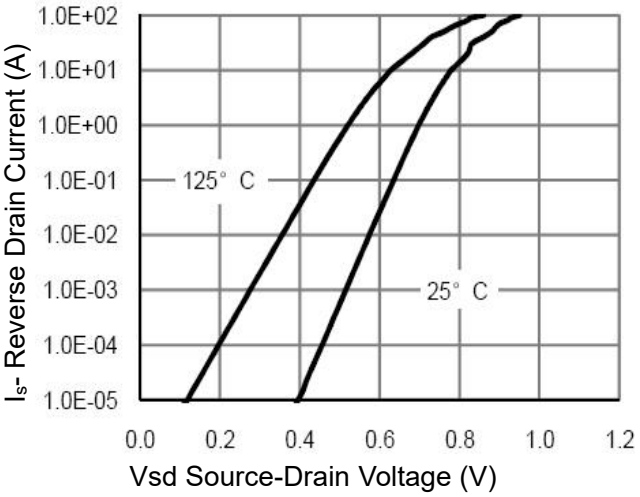



**Figure 6 Source- Drain Diode Forward**

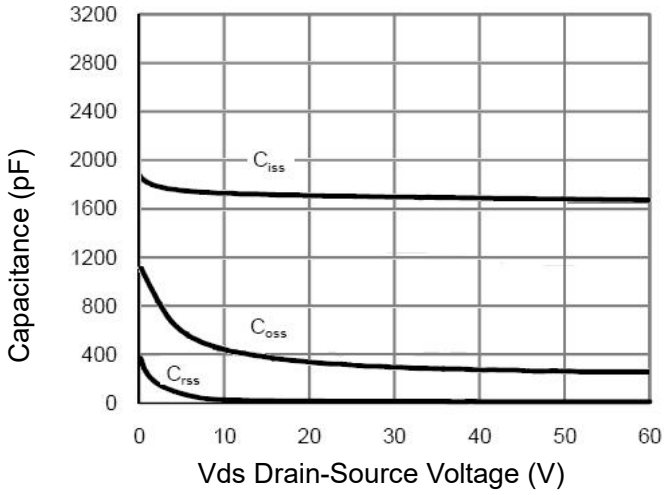



**Figure 7 Capacitance vs Vds**

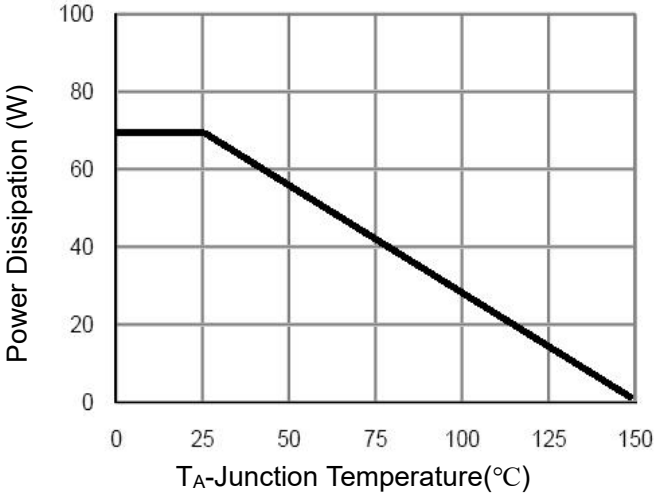



**Figure 9 Power De-rating**

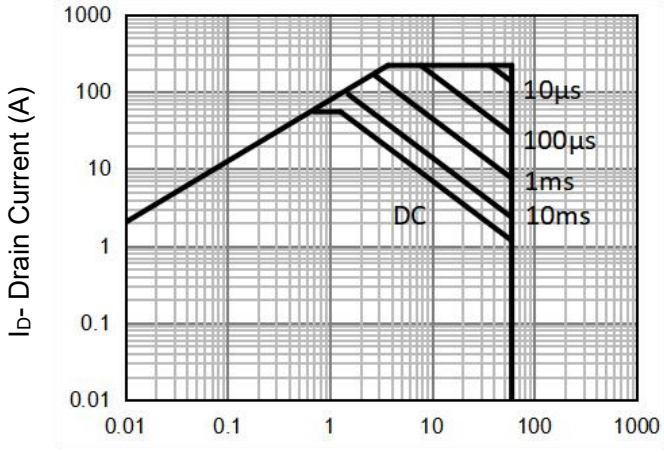



**Figure 8 Safe Operation Area**(Note 3)

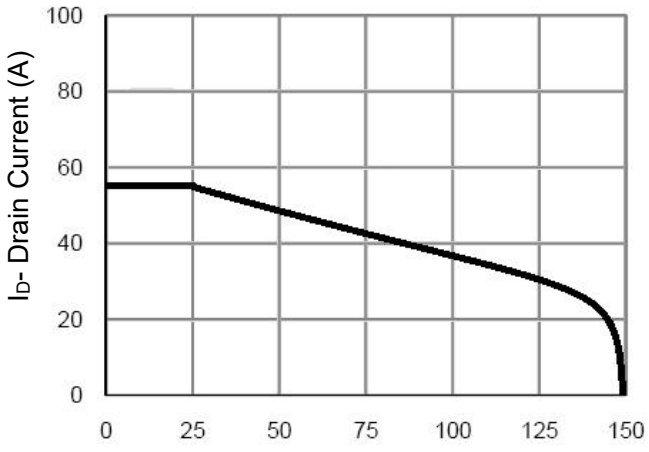



**Figure 10 Current De-rating**

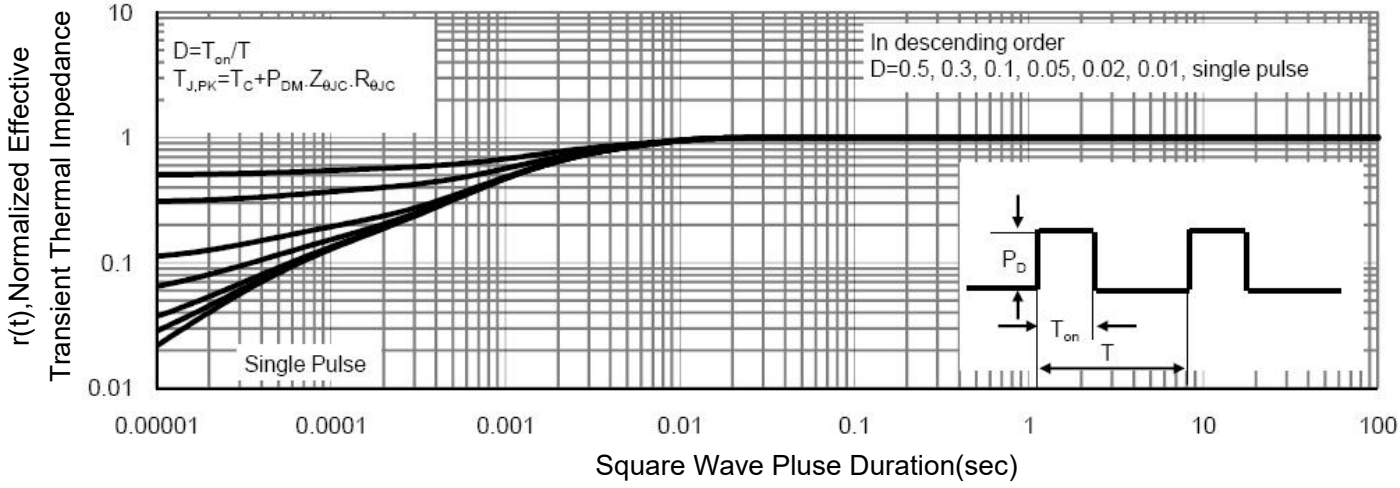
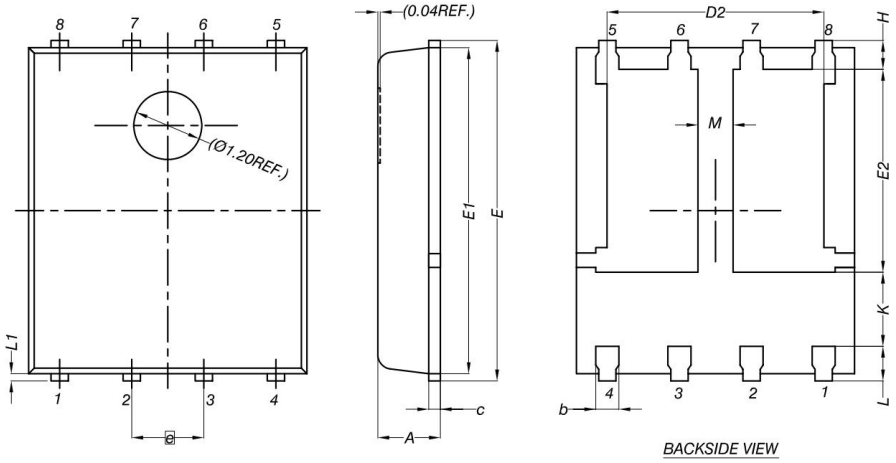
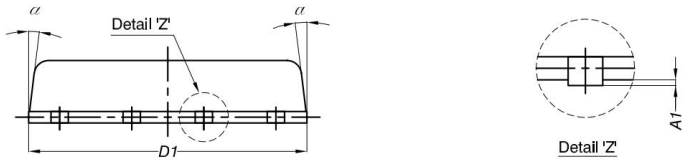


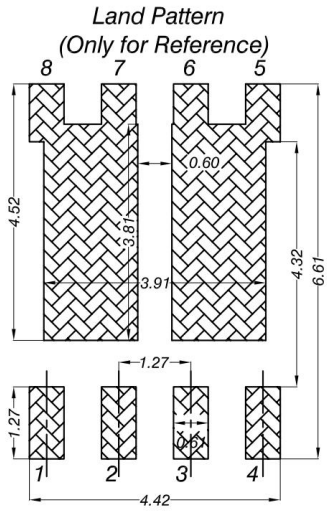

**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L Package Information




| DIM. | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0 | --- | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| C | 0.20 | 0.25 | 0.30 |
| D1 | 4.80 | 4.90 | 5.00 |
| D2 | 3.61 | 3.81 | 3.96 |
| E | 5.90 | 6.00 | 6.10 |
| E1 | 5.70 | 5.75 | 5.80 |
| E2 | 3.38 | 3.58 | 3.78 |
| e | 1.27 BSC | | |
| H | 0.41 | 0.51 | 0.61 |
| K | 1.10 | - | - |
| L | 0.51 | 0.61 | 0.71 |
| L1 | 0.06 | 0.13 | 0.20 |
| M | 0.50 | - | - |
| α | 0° | - | 12° |




Note:
1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
   Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic
   Body Exclusive Of Mold Flash, Tie Bar , Tie Bar Burrs, Gate Burrs And Interlead Flash,
   But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
4. The Package Top May Be Smaller Than The Package Bottom.

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